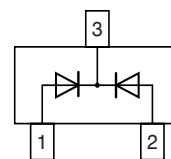
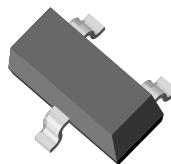


## Dual Varicap Diode

### Features

- Silicon Epitaxial Planar Diode
- Common cathode
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



18108

### Applications

Tuning of separate resonant circuits, push-pull circuits in FM range, especially for car radios

### Mechanical Data

**Case:** SOT-23 Plastic case

**Weight:** approx. 8.1 mg

#### Packaging Codes/Options:

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box

GS08 / 3 k per 7" reel (8 mm tape), 15 k/box

### Parts Table

| Part    | Type differentiation                        | Ordering code                | Marking | Remarks       |
|---------|---|------------------------------|---------|---------------|
| BB804-0 | $V_{RRM} = 20\text{ V}$ , $C_D$ 42-43, 5 pF | BB804-0-GS18 or BB804-0-GS08 | FM0     | Tape and Reel |
| BB804-1 | $V_{RRM} = 20\text{ V}$ , $C_D$ 43-44, 5 pF | BB804-1-GS18 or BB804-1-GS08 | FM1     | Tape and Reel |
| BB804-2 | $V_{RRM} = 20\text{ V}$ , $C_D$ 44-45, 5 pF | BB804-2-GS18 or BB804-2-GS08 | FM2     | Tape and Reel |
| BB804-3 | $V_{RRM} = 20\text{ V}$ , $C_D$ 45-46, 5 pF | BB804-3-GS18 or BB804-3-GS08 | FM3     | Tape and Reel |
| BB804-4 | $V_{RRM} = 20\text{ V}$ , $C_D$ 46-47, 5 pF | BB804-4-GS18 or BB804-4-GS08 | FM4     | Tape and Reel |

1) Any selection part and any marking out of the below listed FM0 to FM4 is possible.

### Absolute Maximum Ratings

$T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified

| Parameter                       | Test condition | Symbol    | Value | Unit |
|---------------------------------|----------------|-----------|-------|------|
| Repetitive peak reverse voltage |                | $V_{RRM}$ | 20    | V    |
| Reverse voltage                 |                | $V_R$     | 18    | V    |
| Forward current                 |                | $I_F$     | 50    | mA   |

### Thermal Characteristics

$T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified

| Parameter                 | Test condition | Symbol    | Value         | Unit             |
|---------------------------|----------------|-----------|---------------|------------------|
| Junction temperature      |                | $T_j$     | 125           | $^\circ\text{C}$ |
| Storage temperature range |                | $T_{stg}$ | - 65 to + 125 | $^\circ\text{C}$ |

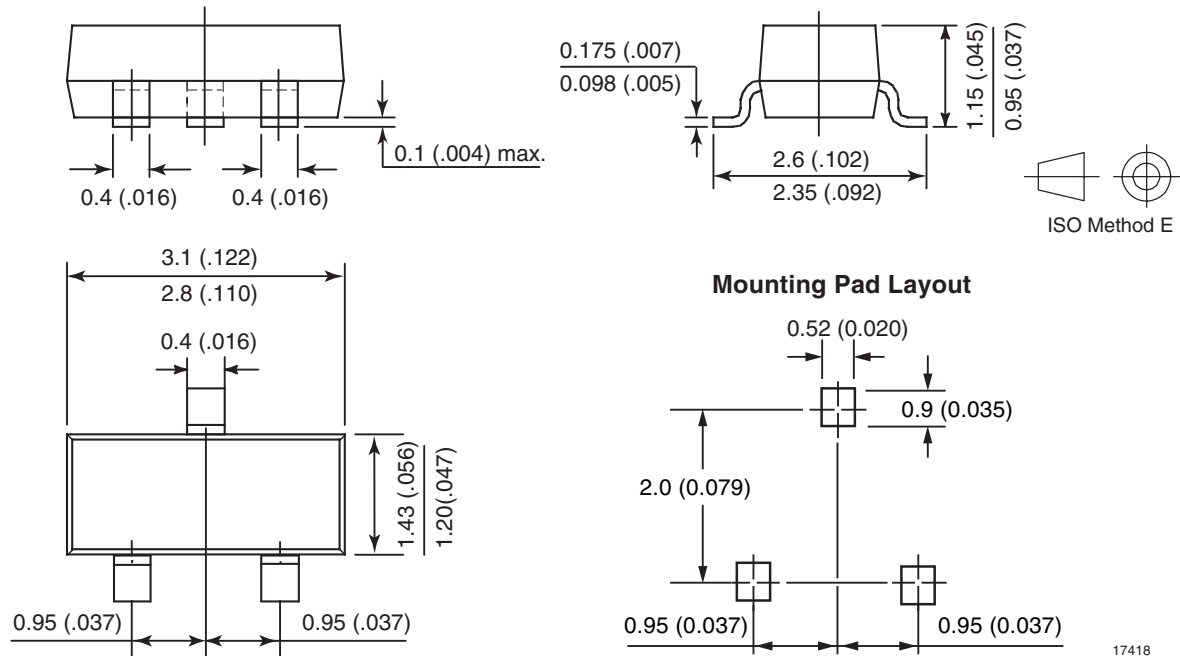
### Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

| Parameter                       | Test condition  | Part    | Symbol          | Min  | Typ. | Max  | Unit          |
|---------------------------------|---|---------|-----------------|------|------|------|---------------|
| Reverse current                 | $V_R = 16\text{ V}$                                   |         | $I_R$           |      |      | 20   | nA            |
|                                 | $V_R = 16\text{ V}, T_j = 60\text{ }^{\circ}\text{C}$ |         | $I_R$           |      |      | 0.2  | $\mu\text{A}$ |
| Diode capacitance <sup>1)</sup> | $V_R = 2\text{ V}, f = 1\text{ MHz}$                  |         | $C_D$           | 42   |      | 47.5 | pF            |
| Diode capacitance               | $V_R = 2\text{ V}, f = 1\text{ MHz}$                  | Group 0 | $C_D$           | 42   |      | 43.5 | pF            |
|                                 |   | Group 1 | $C_D$           | 43   |      | 44.5 | pF            |
|                                 |   | Group 2 | $C_D$           | 44   |      | 45.5 | pF            |
|                                 |   | Group 3 | $C_D$           | 45   |      | 46.5 | pF            |
|                                 |   | Group 4 | $C_D$           | 46   |      | 47.5 | pF            |
| Capacitance ratio               | $V_R = 2\text{ V}, 8\text{ V}, f = 100\text{ MHz}$    |         | $C_{D2}/C_{D8}$ | 1.65 |      | 1.75 |               |
| Series resistance               | $C_D = 38\text{ pF}, f = 100\text{ MHz}$              |         | $r_s$           |      | 0.3  | 0.4  | $\Omega$      |
| Figure of merit                 | $C_D = 38\text{ pF}, f = 100\text{ MHz}$              |         | Q               | 100  | 140  |      |               |

<sup>1)</sup> A packing unit (reel) contains diodes from one capacitance group only. Delivery of single capacitance groups available only on request.

### Package Dimensions in mm (Inches)



## Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design  
and may do so without further notice.

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